

Descriptions

Double silicon PNP transistor in a SOT-363 Plastic Package.

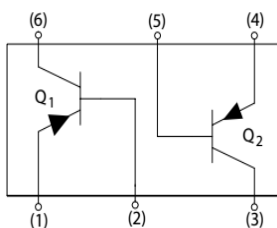
Features

High voltage, complementary Pair with MMBT5551DW.

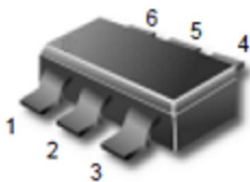
Applications

General purpose high voltage amplifier.

Equivalent Circuit



Pinning



PIN 1、 4 : Emitter

PIN 2、 5 : Base

PIN 3、 6 : Collector

h_{FE} Classifications & Marking

See Marking Instructions.

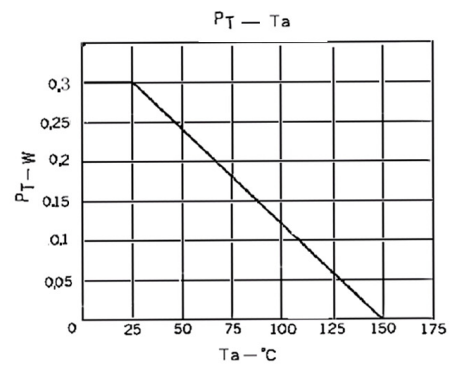
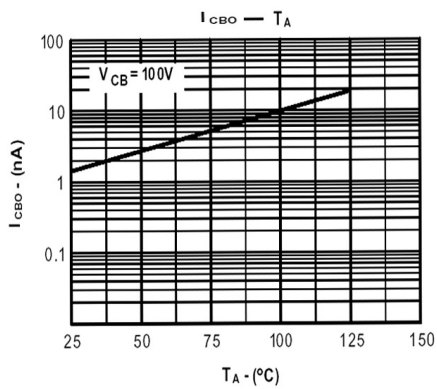
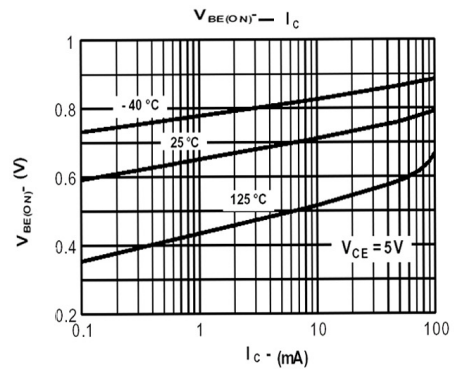
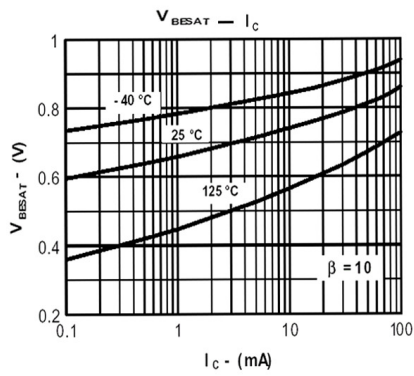
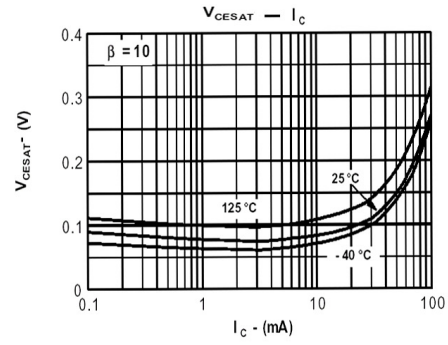
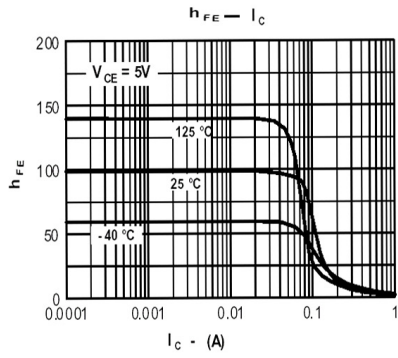
Absolute Maximum Ratings(Ta=25°C)

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-180	V
Collector to Emitter Voltage	V_{CEO}	-160	V
Emitter to Base Voltage	V_{EBO}	-6.0	V
Collector Current	I_C	-600	mA
Base Current	I_B	-300	mA
Collector Power Dissipation	P_C	300	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	-55~150	°C

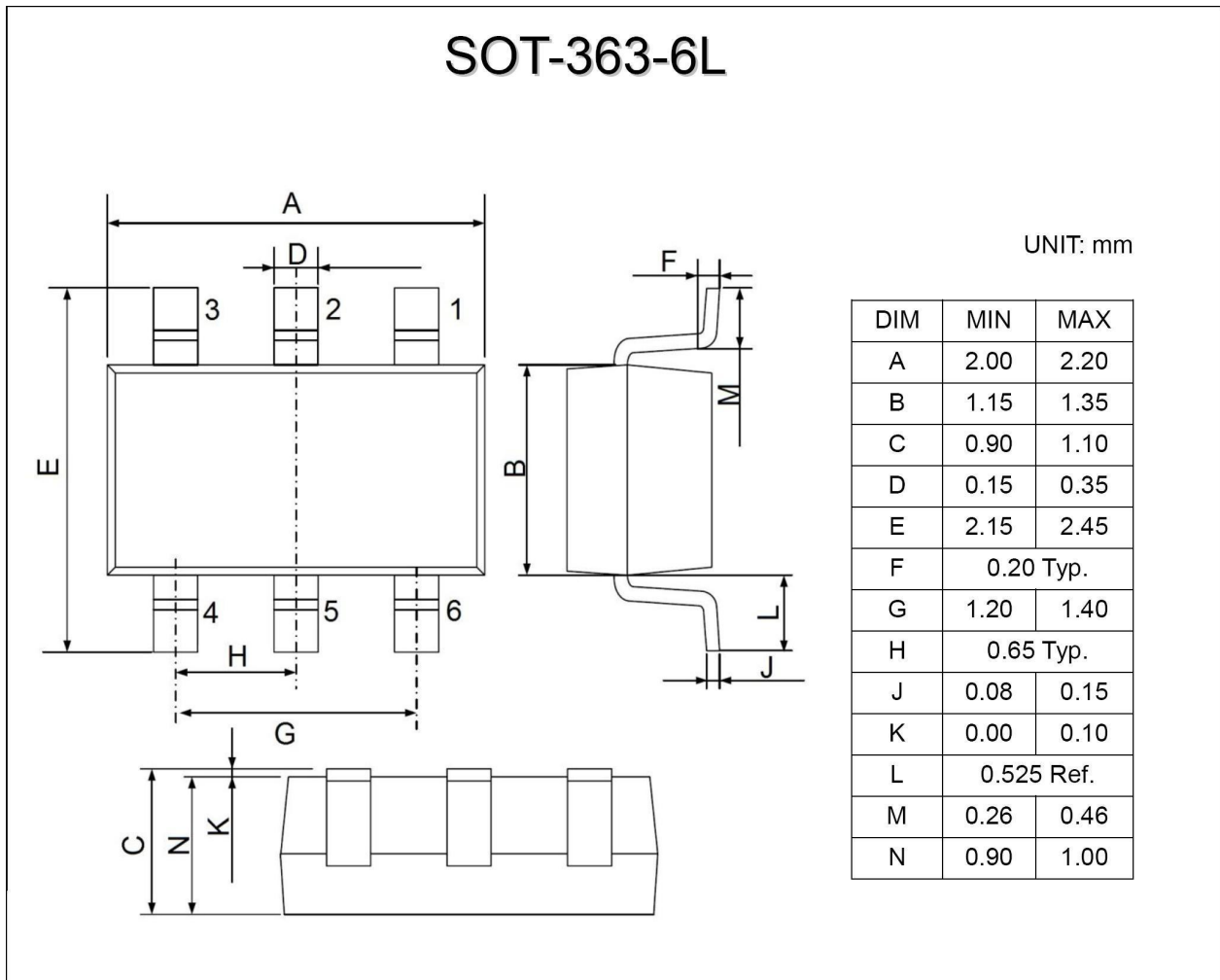
Electrical Characteristics(Ta=25°C)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cut-Off Current	I_{CBO}	$V_{CB}=-180V$ $I_E=0$			-0.1	μA
Emitter Cut-Off Current	I_{EBO}	$V_{EB}=-6.0V$ $I_C=0$			-0.1	μA
DC Current Gain	$h_{FE(1)}$	$V_{CE}=-5.0V$ $I_C=-10mA$	100		300	
	$h_{FE(2)}$	$V_{CE}=-5.0V$ $I_C=-50mA$	20	70		
	$h_{FE(3)}$	$V_{CE}=-5.0V$ $I_C=-1.0mA$	40	180		
Collector-Emitter Saturation Voltage	$V_{CE(sat)(1)}$	$I_C=-10mA$ $I_B=-1.0mA$		-0.12	-0.4	V
	$V_{CE(sat)(2)}$	$I_C=-50mA$ $I_B=-5.0mA$		-0.5	-0.8	V
Base-Emitter Saturation Voltage	$V_{BE(sat)(1)}$	$I_C=-10mA$ $I_B=-1.0mA$		-0.75	-1.0	V
	$V_{BE(sat)(2)}$	$I_C=-50mA$ $I_B=-5.0mA$		-0.8	-1.0	V
Base-Emitter Voltage	V_{BE}	$V_{CE}=-5.0V$ $I_C=-10mA$		-0.7	-0.75	V
Transition Frequency	f_T	$V_{CE}=-10V$ $I_C=-10mA$	100		200	MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=-10V$ $I_E=0$ $f=10MHz$		2.5	5.0	pF
Turn-on Time	t_{on}	$I_C=-100mA$ $-I_{B1}=I_{B2}=-10mA$		0.1		μs
Storage Time	t_{off}			0.2		μs
Fall Time	t_{stg}			0.1		μs

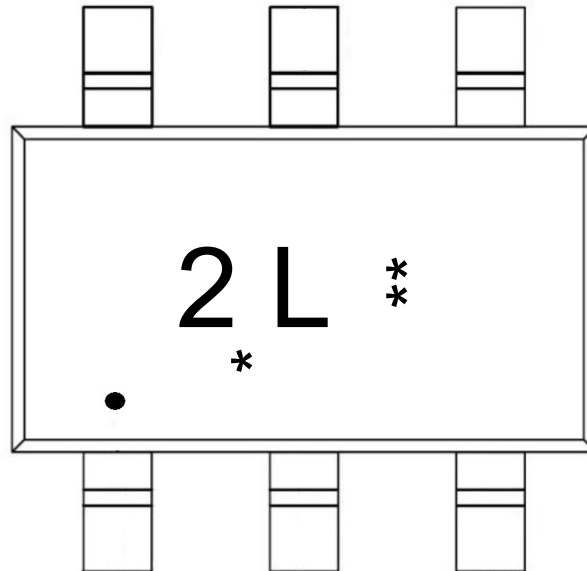
Electrical Characteristic Curve



Package Dimensions



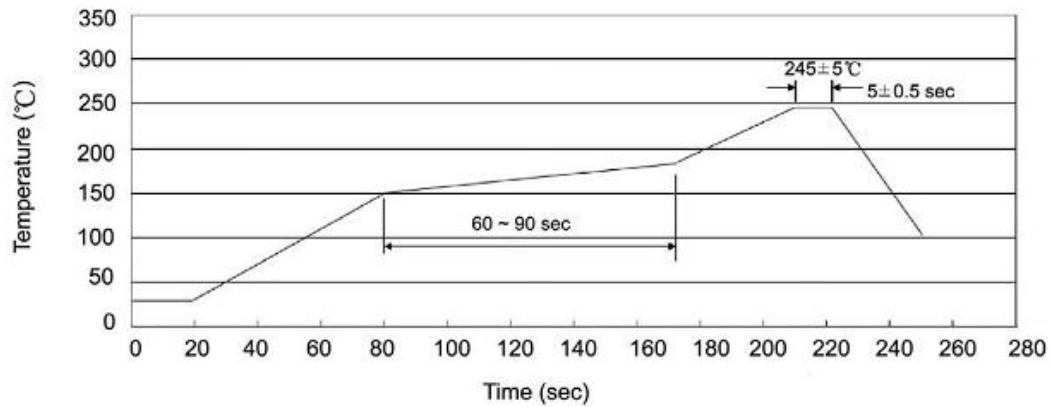
Marking Instructions



Note:

- : "1" Pin
- 2L : Product Type Code
- ***: Lot No. Code, code change with Lot No.

Temperature Profile for IR Reflow Soldering(Pb-Free)



Note:

1. Preheating: 150~180°C, Time: 60~90sec.
2. Peak Temp.: 245±5°C, Duration: 5±0.5sec.
3. Cooling Speed: 2~10°C/sec.

Resistance to Soldering Heat Test Conditions

Temp.: 260±5°C Time: 10±1 sec

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